

## FDP5690/FDB5690

### 60V N-Channel PowerTrench™MOSFET

### **General Description**

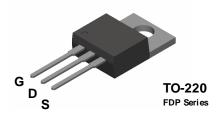
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

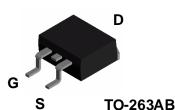
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\scriptscriptstyle DS(on)}$  specifications resulting in DC/DC power supply designs with higher overall efficiency.

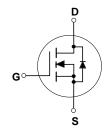
#### **Features**

- 32 A, 60 V.  $R_{DS(ON)} = 0.027~\Omega$  @  $V_{GS} = 10~V$   $R_{DS(ON)} = 0.032~\Omega$  @  $V_{GS} = 6~V$ .
- Critical DC electrical parameters specified at evevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low  $\boldsymbol{R}_{_{DS(DN)}}.$
- 175°C maximum junction temperature rating.

**FDB Series** 







### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FDP5690	FDB5690	Units
V <sub>DSS</sub>	Drain-Source Voltage	6	60	V
V <sub>GSS</sub>	Gate-Source Voltage	±	20	V
I <sub>D</sub>	Maximum Drain Current - Continuous	3	Α	
	- Pulsed	1		
P <sub>D</sub>	Total Power Dissipation @ T <sub>C</sub> = 25°C	5	W	
	Derate above 25°C	0	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-65 to	+175	°C

### **Thermal Characteristics**

R <sub>e</sub> JC	Thermal Resistance, Junction-to-Case	2.6	°C/W
$R_{eJA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB5690	FDB5690	13"	24mm	800
FDP5690	FDP5690	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (No	ote1)				
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 30 \text{ V}, I_{D} = 32 \text{A}$			80	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche	Current			32	Α
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250  \mu\text{A}$	60			V
<u>A</u> BVnss ΔTJ	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		61		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V			1	μА
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 1)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250  \mu A$	2	2.4	4	V
<u>A</u> VGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-6.4		mV/º(
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}, V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 6 \text{ V}, I_D = 15 \text{ A}$		0.021 0.042 0.024	0.027 0.055 0.032	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	50			Α
<b>G</b> FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 16 \text{ A}$		32		S
Dvnamio	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1120		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		160		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			80		pF
Switchin	g Characteristics (Note 1)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_D = 1 \text{ A},$		10	18	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			24	39	ns
t <sub>f</sub>	Turn-Off Fall Time	]		10	18	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 15 V,		23	33	nC
$Q_{gs}$	Gate-Source Charge	$I_D = 16 \text{ A}, V_{GS} = 10 \text{ V}$		3.9		nC
$Q_{gd}$	Gate-Drain Charge			6.8		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
I <sub>s</sub>	Maximum Continuous Drain-Source	_			32	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 16 \text{ A}$ (Note 1)		0.92	1.2	V

<sup>1.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

## **Typical Characteristics**

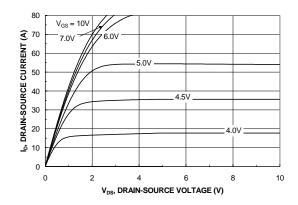


Figure 1. On-Region Characteristics.

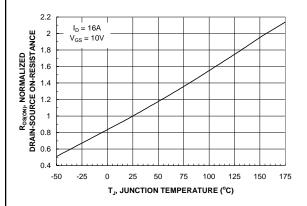


Figure 3. On-Resistance Variation with Temperature.

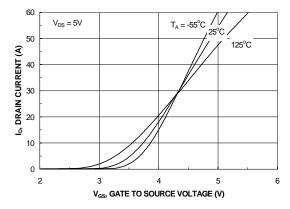


Figure 5. Transfer Characteristics.

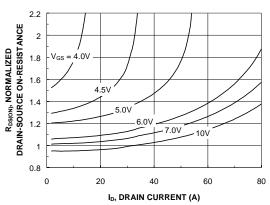


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

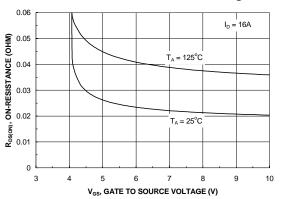


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

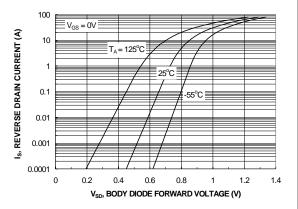
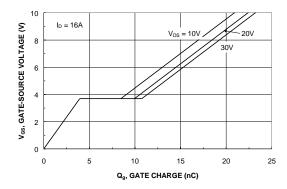


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.





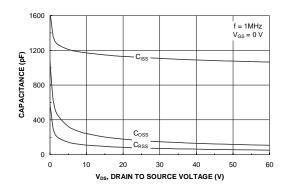


Figure 7. Gate-Charge Characteristics.

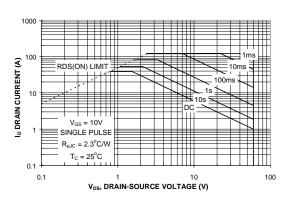


Figure 8. Capacitance Characteristics.

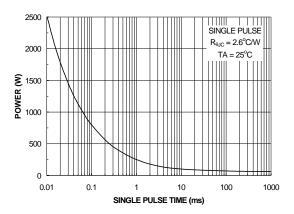
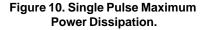


Figure 9. Maximum Safe Operating Area.



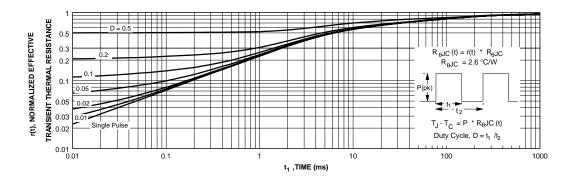
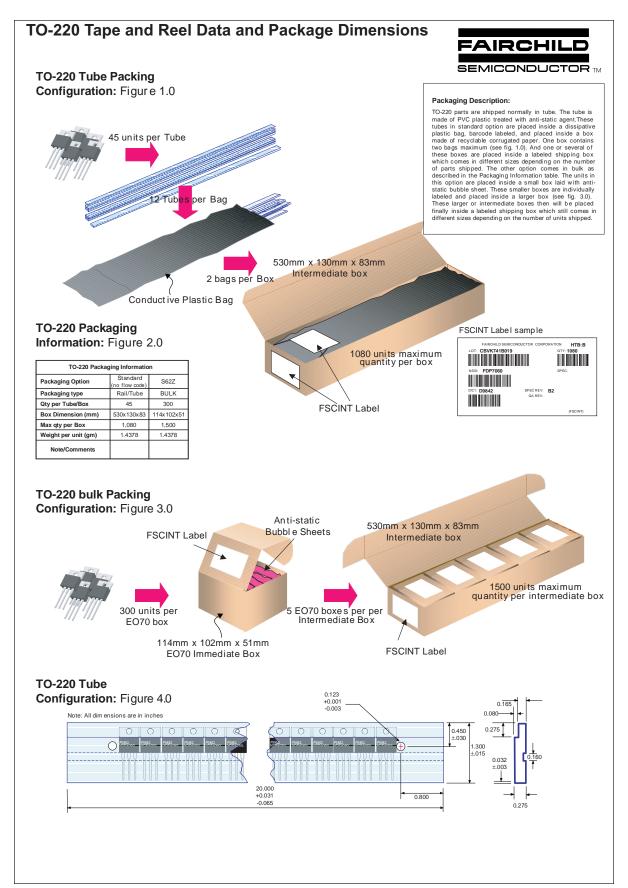
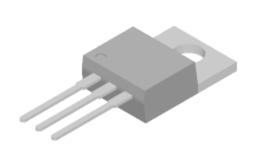


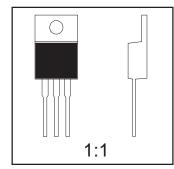
Figure 11. Transient Thermal Response Curve.



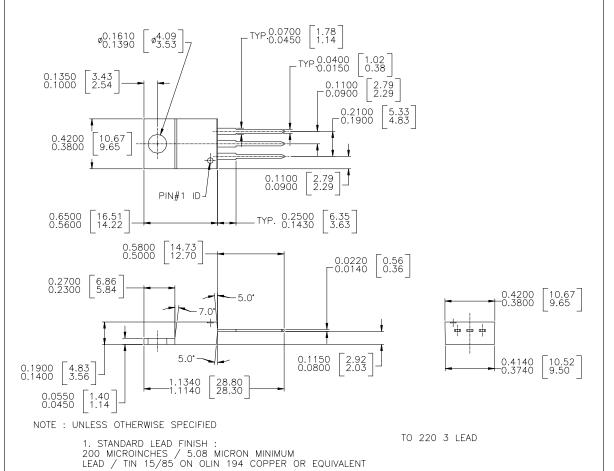
## TO-220 Tape and Reel Data and Package Dimensions, continued

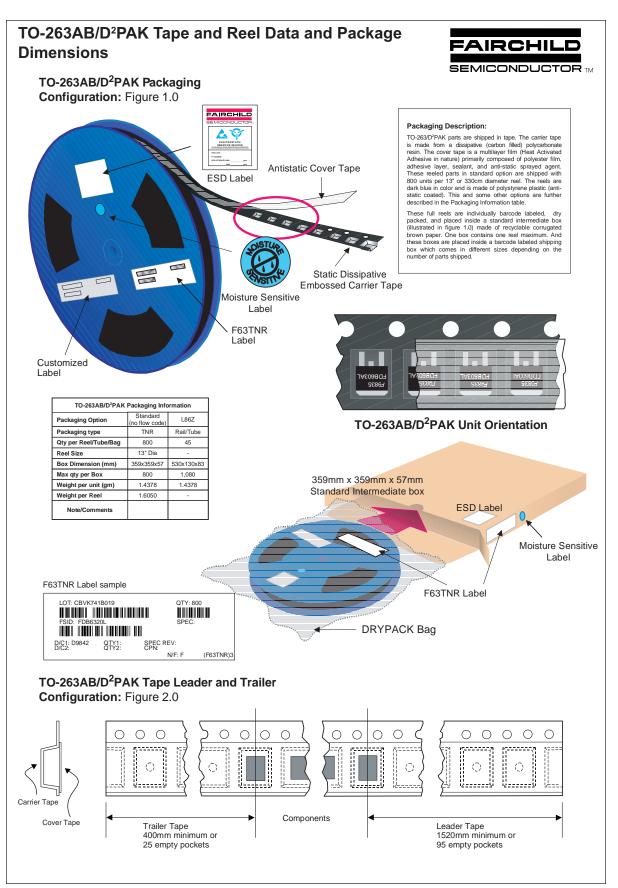
## TO-220 (FS PKG Code 37)



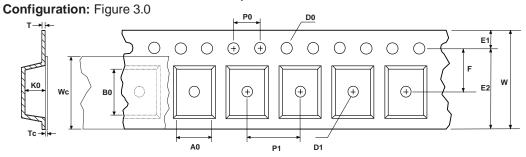


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]





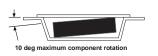
### TO-263AB/D<sup>2</sup>PAK Embossed Carrier Tape



## User Direction of Feed

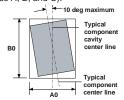
					Dim	ensions	are in mi	illimeter						
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D <sup>2</sup> PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation

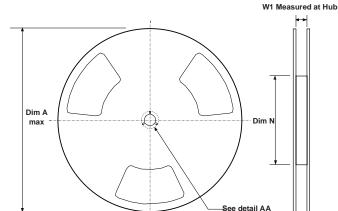


Sketch B (Top View)
Component Rotation

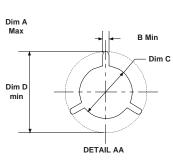


Sketch C (Top View)
Component lateral movement

# **TO-263AB/D<sup>2</sup>PAK Reel Configuration:** Figure 4.0



13" Diameter Option

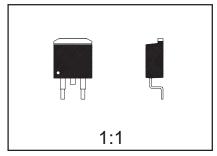


W2 max Measured at Hub

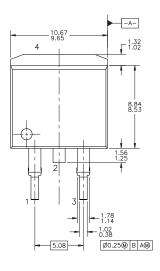
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

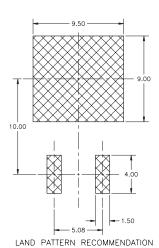
# TO-263AB/D<sup>2</sup>PAK (FS PKG Code 45)

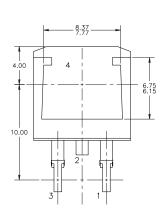


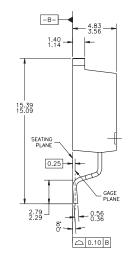


Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]









- NOTES: UNLESS OTHERWISE SPECIFIED

  A) ALL DIMENSIONS ARE IN MILLIMETERS.
  B) STANDARD LEAD FINISH:
  200 MICROINCHES / 5.08 MICROMETERS MIN.
  LEAD/TIN 15/85 ON OLIN 194 COPPER OR
  EQUIVALENT.
  C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
  TO EXCEED 0.003 INCH / 0.05mm.
  D) NO PACKAGE CHIPS, CRACKS OR SURFACE
  IDENTIFICATION ALLOWED AFTER FORMING.
  E) REFERENCE JEDEC, TO—265, ISSUE C,
  VARIATION AB, DATED 2/92.

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT™ QFET™ FACT Quiet Series™ QS™

 $\begin{array}{lll} \mathsf{FAST}^{\circledast} & \mathsf{Quiet\,Series^{\mathsf{TM}}} \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}3} \\ \mathsf{GTO^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}6} \\ \mathsf{HiSeC^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}8} \\ \end{array}$ 

#### **DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

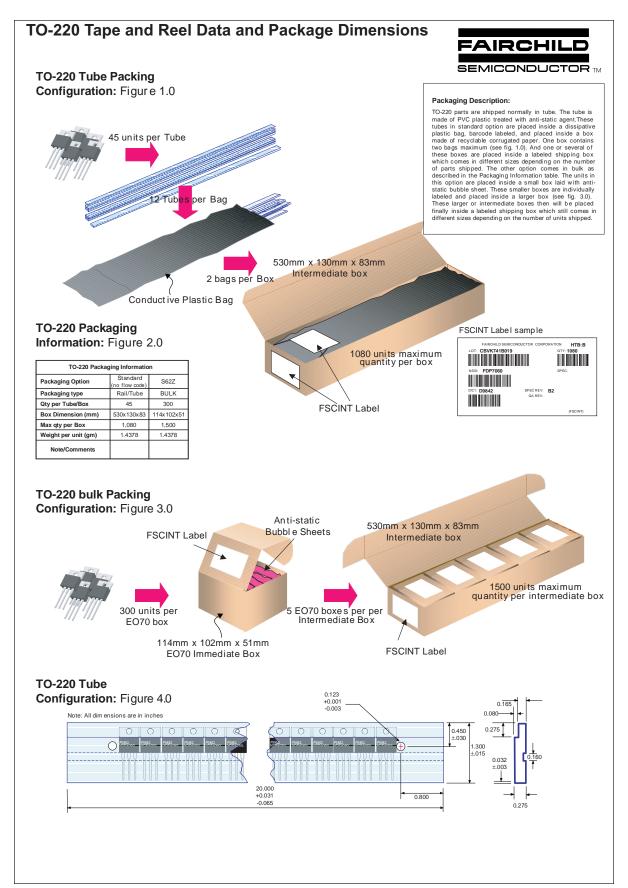
1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

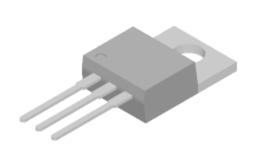
#### **Definition of Terms**

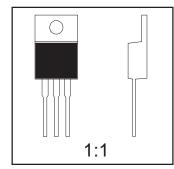
Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



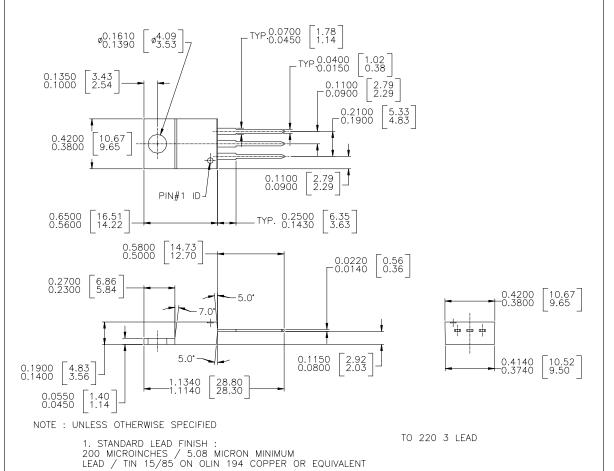
## TO-220 Tape and Reel Data and Package Dimensions, continued

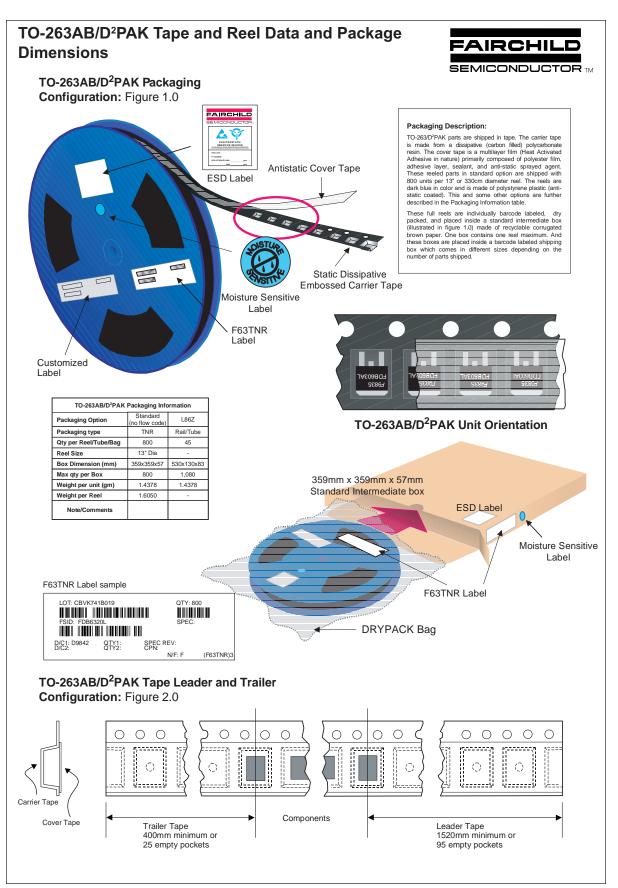
## TO-220 (FS PKG Code 37)



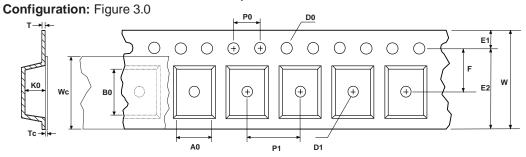


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]





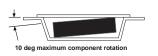
### TO-263AB/D<sup>2</sup>PAK Embossed Carrier Tape



## User Direction of Feed

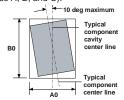
					Dim	ensions	are in mi	illimeter						
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D <sup>2</sup> PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation

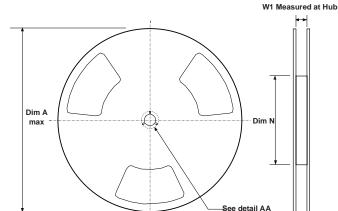


Sketch B (Top View)
Component Rotation

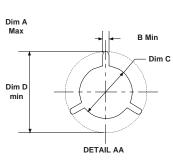


Sketch C (Top View)
Component lateral movement

# **TO-263AB/D<sup>2</sup>PAK Reel Configuration:** Figure 4.0



13" Diameter Option

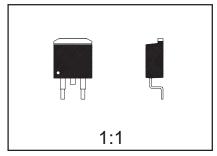


W2 max Measured at Hub

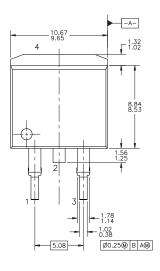
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

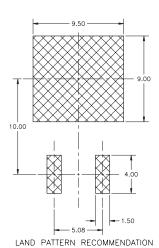
# TO-263AB/D<sup>2</sup>PAK (FS PKG Code 45)

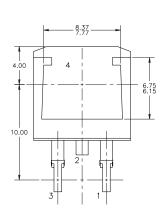


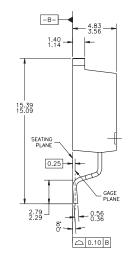


Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]









- NOTES: UNLESS OTHERWISE SPECIFIED

  A) ALL DIMENSIONS ARE IN MILLIMETERS.
  B) STANDARD LEAD FINISH:
  200 MICROINCHES / 5.08 MICROMETERS MIN.
  LEAD/TIN 15/85 ON OLIN 194 COPPER OR
  EQUIVALENT.
  C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
  TO EXCEED 0.003 INCH / 0.05mm.
  D) NO PACKAGE CHIPS, CRACKS OR SURFACE
  IDENTIFICATION ALLOWED AFTER FORMING.
  E) REFERENCE JEDEC, TO—265, ISSUE C,
  VARIATION AB, DATED 2/92.

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT™ QFET™ FACT Quiet Series™ QS™

FAST<sup>®</sup> Quiet Series<sup>™</sup> SuperSOT<sup>™</sup>-3 GTO<sup>™</sup> SuperSOT<sup>™</sup>-6

#### **DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.